BLC8G27LS-210PV

Power LDMOS transistor

Rev. 1 — 9 February 2015 **Product data sheet**

1. Product profile

1.1 General description

200 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 2500 MHz to 2700 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Test signal	f	I_{Dq}	V_{DS}	$P_{L(AV)}$	G_p	η_D	$ACPR_{5M}$
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2600 to 2700	1730	28	65	17	30	–29 [1]

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF per carrier; 5 MHz carrier spacing.

1.2 Features and benefits

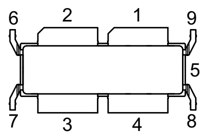
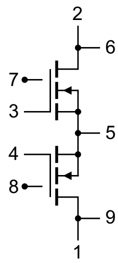
- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth performance (150 MHz typical)
- Designed for broadband operation (2500 MHz to 2700 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- RF power amplifiers for base stations and multi carrier applications in the 2500 MHz to 2700 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain2		 aaa-009150
2	drain1		
3	gate1		
4	gate2		
5	source [1]		
6	video decoupling drain1		
7	n.c.		
8	n.c.		
9	video decoupling drain2		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLC8G27LS-210PV	-	air cavity plastic earless flanged package; 8 leads	SOT1251-3

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		–0.5	+13	V
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature	[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 65 W	0.22	K/W

6. Characteristics

Table 6. DC characteristics

T_j = 25 °C per section, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 1.44 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 144 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 865 mA	1.6	2	2.4	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	2.8	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	26.9	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	280	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 7.2 A	-	11.2	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)}$ + 3.75 V; I_D = 5.4 A	-	0.10	-	Ω

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; 3GPP test model 1 with 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF; f_1 = 2602.5 MHz; f_2 = 2607.5 MHz; f_3 = 2692.5 MHz; f_4 = 2697.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 1730 mA; T_{case} = 25 °C; unless otherwise specified; in a water cooled class-AB test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)}$ = 65 W	15.8	17	-	dB
η_D	drain efficiency	$P_{L(AV)}$ = 65 W	27	30	-	%
RL_{in}	input return loss	$P_{L(AV)}$ = 65 W	-	–13	–8	dB
$ACPR_{5M}$	adjacent channel power ratio (5 MHz)	$P_{L(AV)}$ = 65 W	-	–29	–26	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLC8G27LS-210PV is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 1730 mA; P_L = 200 W (CW); f = 2600 MHz.

7.2 Impedance information

Table 8. Typical impedance

Measured load-pull data per section; I_{Dq} = 865 mA; V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]
(MHz)	(Ω)	(Ω)
2500	2.58 – j5.80	1.60 – j4.32
2600	3.40 – j6.30	1.65 – j4.44
2700	6.35 – j6.45	1.77 – j4.75

[1] Z_S and Z_L defined in Figure 1.

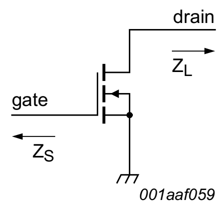
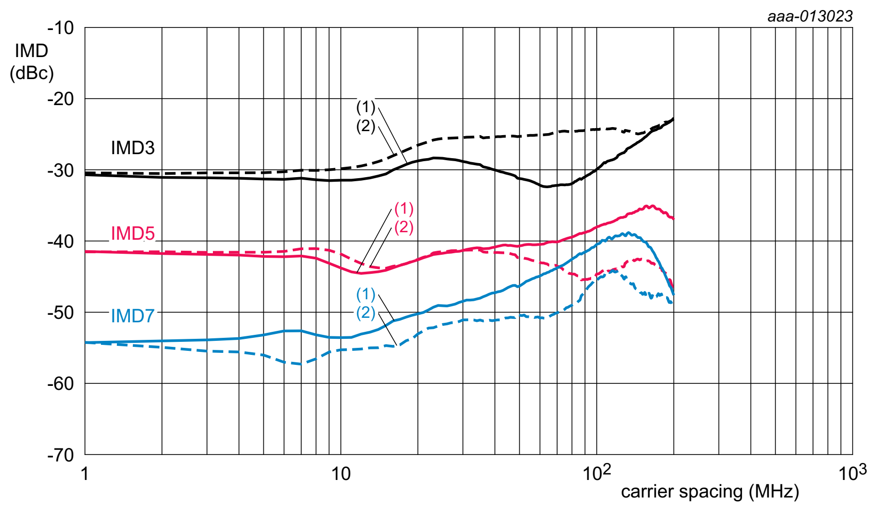


Fig 1. Definition of transistor impedance

7.3 VBW in a class-AB operation

The BLC8G27LS-210PV shows 150 MHz (typical) video bandwidth (IMD third-order intermodulation inflection point) in a class-AB test circuit in the 2.6 GHz to 2.7 GHz band at V_{DS} = 28 V and I_{Dq} = 1.73 A.



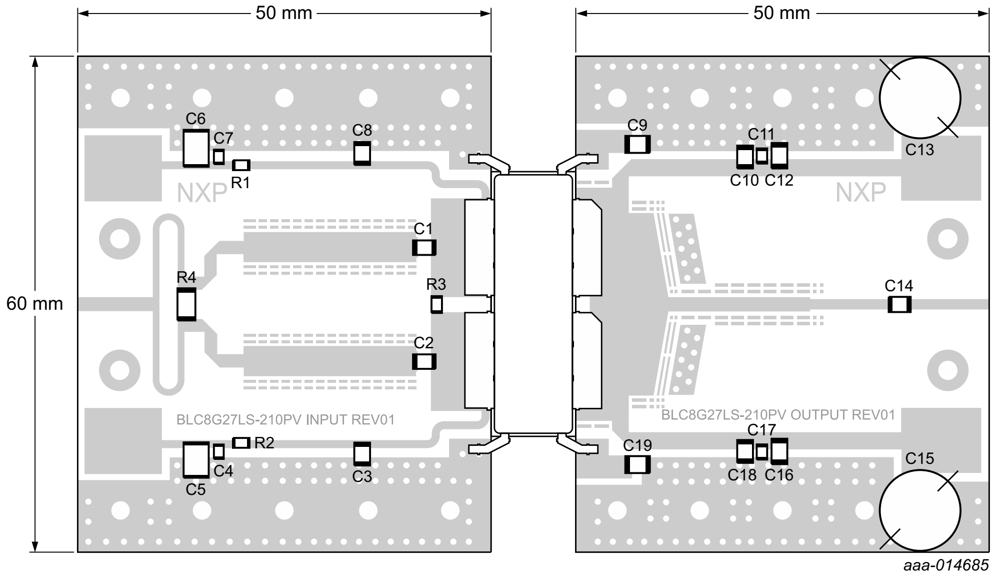
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) low

(2) high

Fig 2. VBW capacity in class-AB test circuit

7.4 Test circuit



Printed-Circuit Board (PCB): Rogers 4350B with a thickness of 0.76 mm. See Table 9 for a list of components.

Fig 3. Component layout

Table 9. List of components

See Figure 3 for component layout.

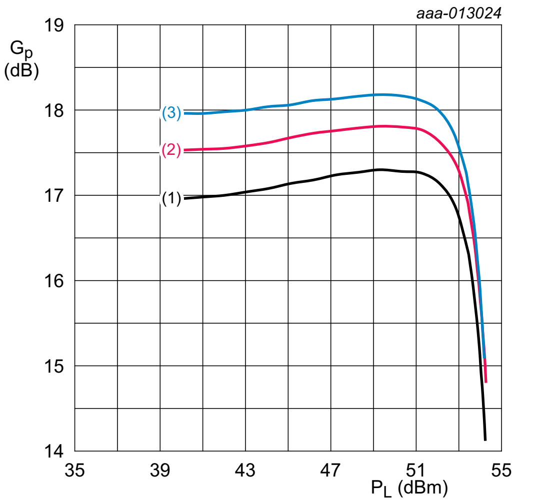
Component	Description	Value		Remarks
C1, C2	multilayer ceramic chip capacitor	1.6 pF	[1]	ATC 800B
C3, C8, C10, C14, C18	multilayer ceramic chip capacitor	24 pF	[1]	ATC 800B
C4, C7	multilayer ceramic chip capacitor	100 nF	[2]	Murata
C5, C6	multilayer ceramic chip capacitor	1 μF	[2]	Murata
C9, C12, C16, C19	multilayer ceramic chip capacitor	470 μF, 50 V	[2]	Murata
C11, C17	multilayer ceramic chip capacitor	220 nF	[2]	Murata
C13, C15	electrolytic capacitor	> 470 μF, 63 V		
R1, R2	chip resistor	4.7 Ω, 1 % tolerance		SMD 0805
R3	chip resistor	10 Ω, 1 % tolerance		SMD 0805
R4	chip resistor	100 Ω, 1 % tolerance		SMD 2010

[1] American Technical Ceramics type 800B or capacitor of same quality.

[2] Murata or capacitor of same quality.

7.5 Graphical data

7.5.1 Pulsed CW



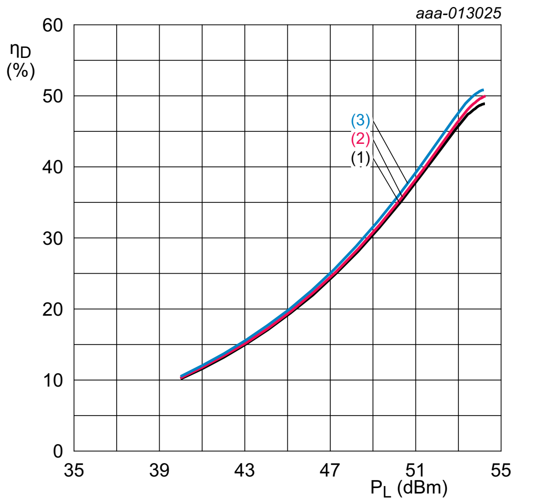
V_{DS} = 28 V; I_{Dq} = 1730 mA; t_p = 100 μs; δ = 10 %.

(1) f = 2600 MHz

(2) f = 2650 MHz

(3) f = 2700 MHz

Fig 4. Power gain as a function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 1730 mA; t_p = 100 μs; δ = 10 %.

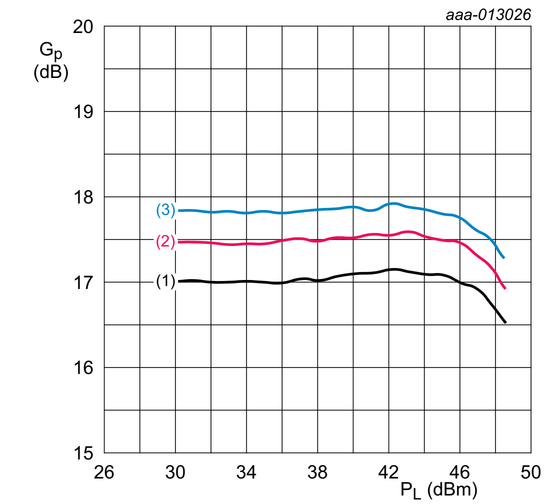
(1) f = 2600 MHz

(2) f = 2650 MHz

(3) f = 2700 MHz

Fig 5. Drain efficiency as a function of out power; typical values

7.5.2 IS-95



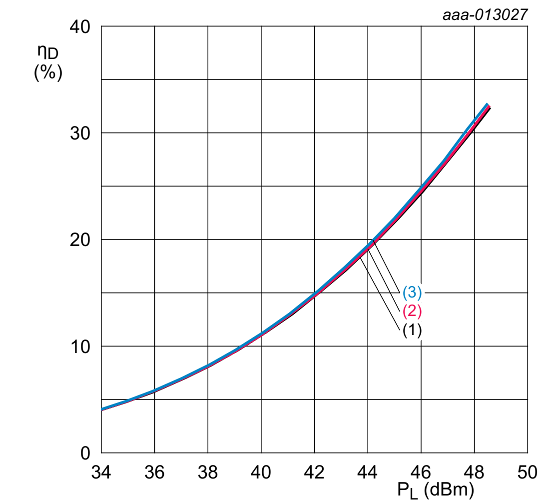
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 6. Power gain as a function of output power; typical values



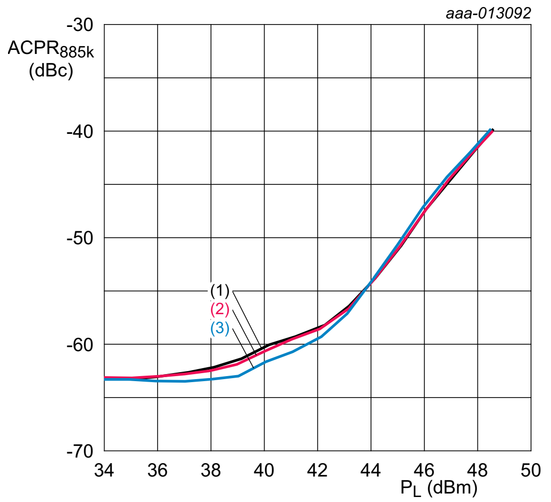
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 7. Drain efficiency as a function of output power; typical values



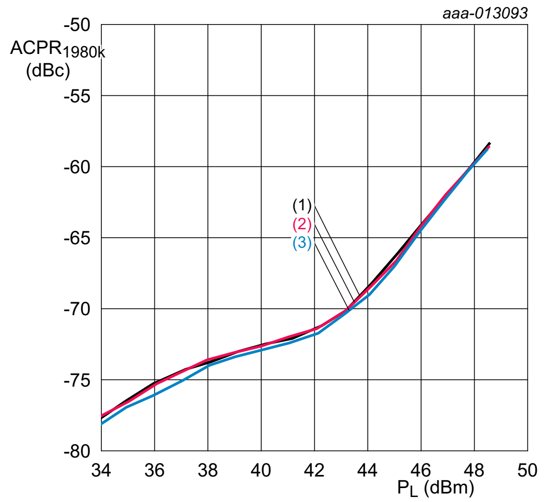
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 8. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



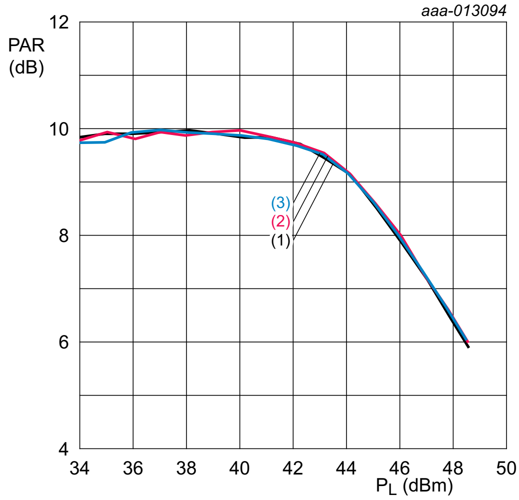
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 9. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values



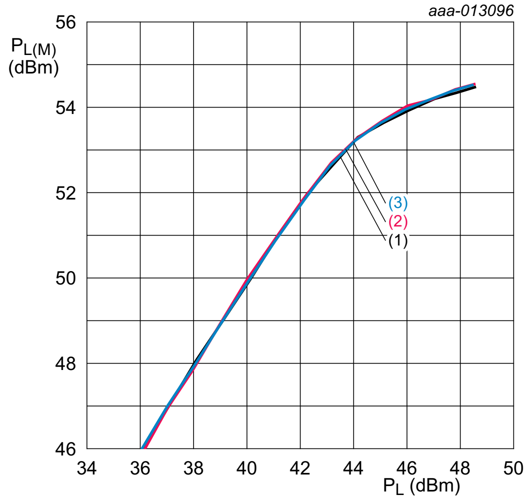
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 10. Peak-to-average ratio as a function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 1730 mA.

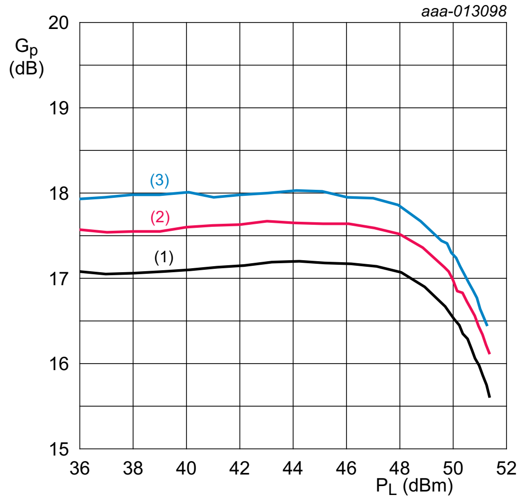
(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 11. Peak output power as a function of output power; typical values

7.5.3 1-Carrier W-CDMA



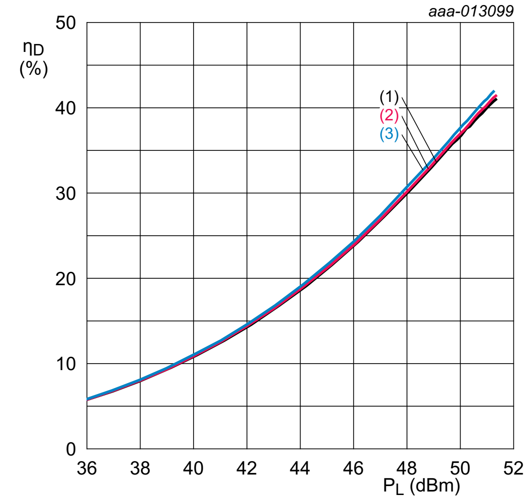
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2602.5 MHz

(2) f = 2650 MHz

(3) f = 2697.5 MHz

Fig 12. Power gain as a function of output power; typical values



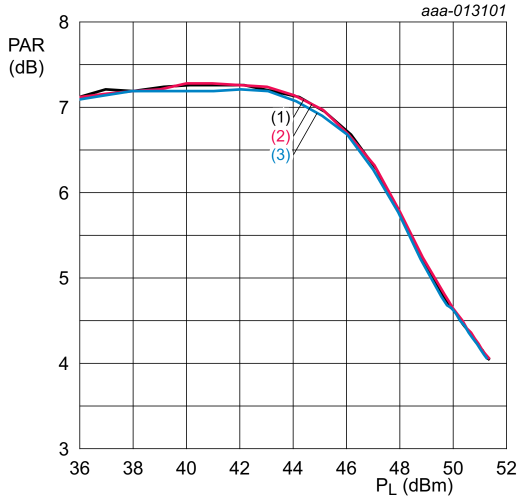
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2602.5 MHz

(2) f = 2650 MHz

(3) f = 2697.5 MHz

Fig 13. Drain efficiency as a function of output power; typical values



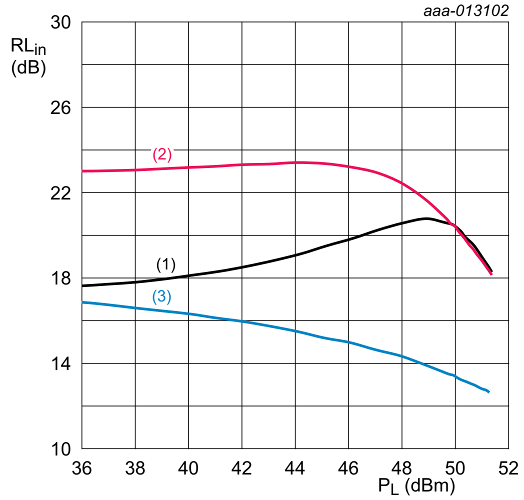
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2602.5 MHz

(2) f = 2650 MHz

(3) f = 2697.5 MHz

Fig 14. Peak-to-average ratio as a function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 1730 mA.

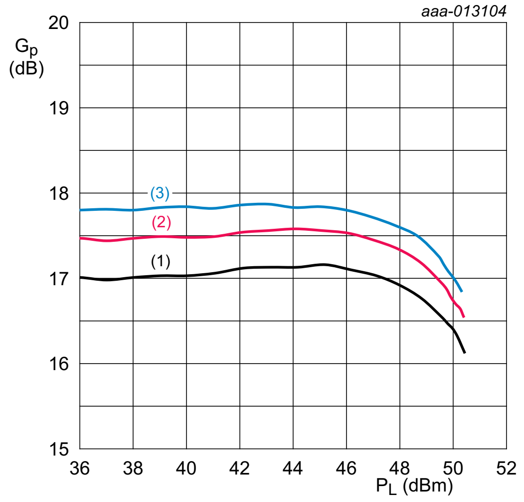
(1) f = 2602.5 MHz

(2) f = 2650 MHz

(3) f = 2697.5 MHz

Fig 15. Input return loss as a function of output power; typical values

7.5.4 2-Carrier W-CDMA



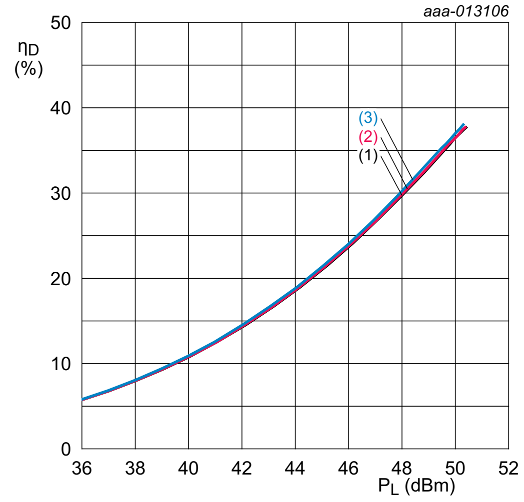
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 16. Power gain as a function of output power; typical values



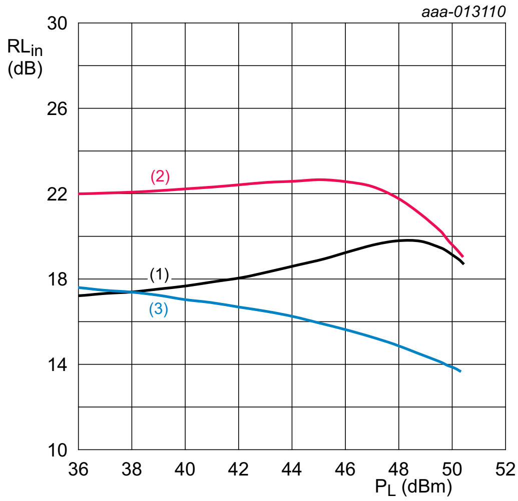
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 17. Drain efficiency as a function of output power; typical values



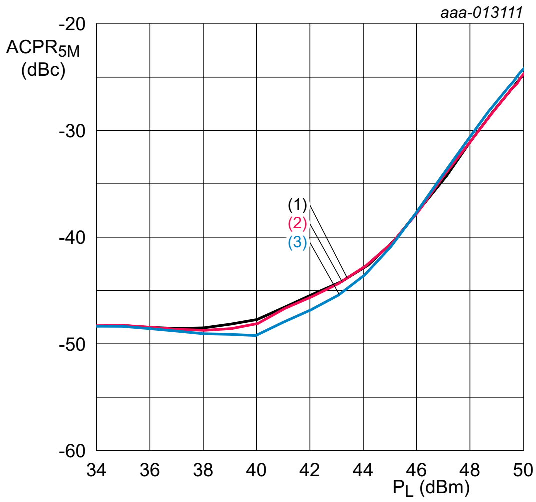
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 18. Input return loss as a function of output power; typical values



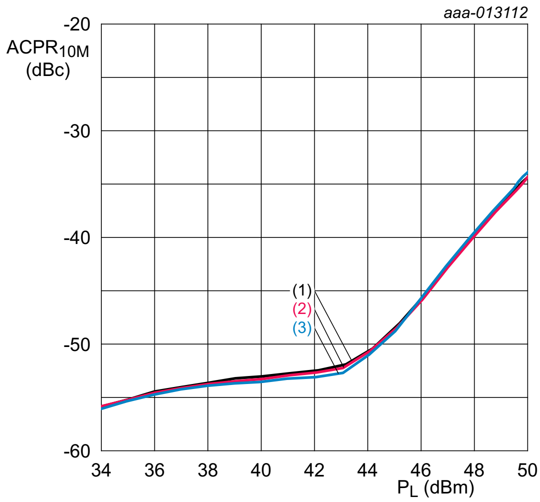
V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 19. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 1730 mA.

(1) f = 2605 MHz

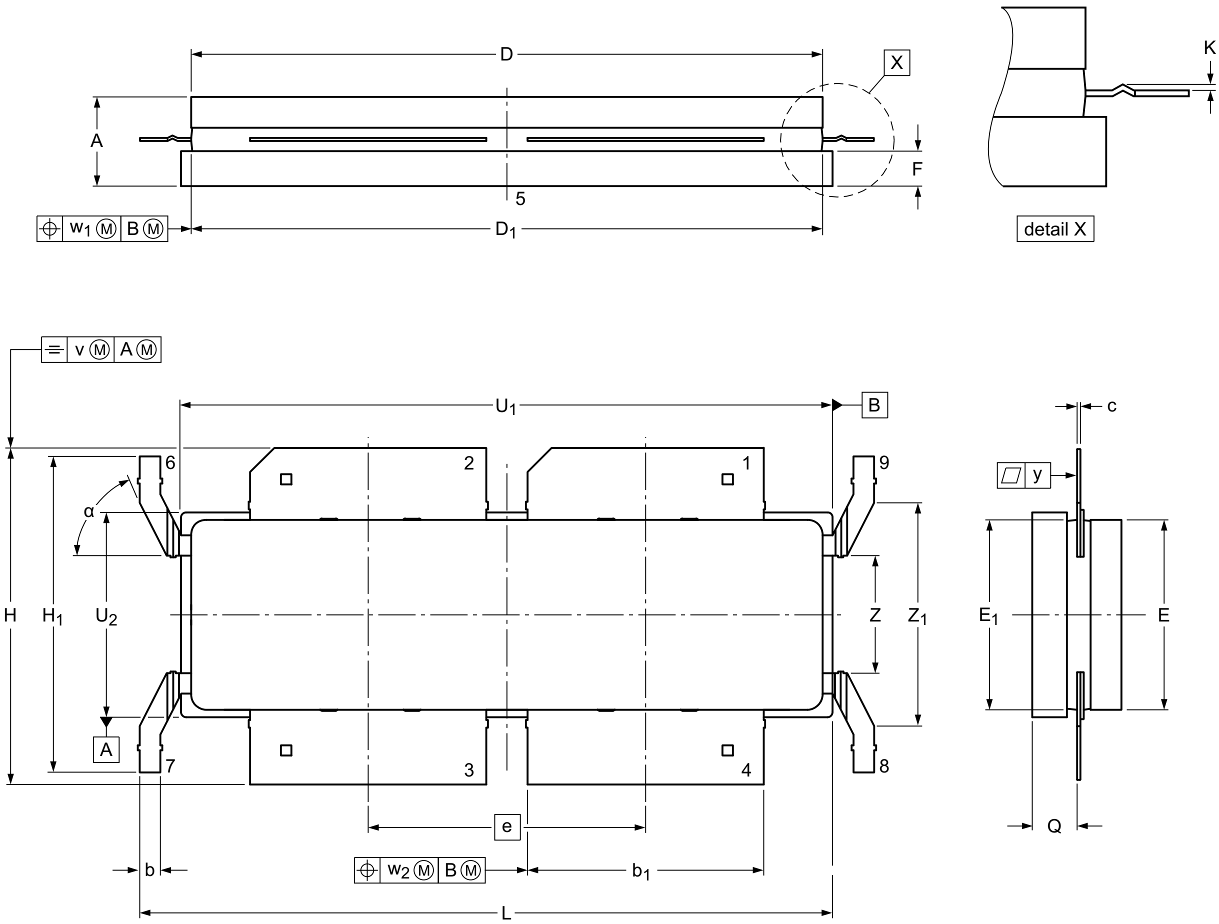
(2) f = 2650 MHz

(3) f = 2695 MHz

Fig 20. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

8. Package outline

Air cavity plastic earless flanged package; 8 leads **SOT1251-3**



K	y	α	Z	Z_1
0.17	0.1	65°	5.94	11.18
		61°	5.74	10.97

0 10 mm
scale

Dimensions (mm are the original dimensions)

Unit(1)		A	b	b_1	c	D	D_1	E	E_1	e	L	F	H	H_1	Q	U_1	U_2	v	w_1	w_2
mm	max	4.65	1.12	11.78	0.2	31.44	31.34	9.60	9.50		36.42	1.83	16.71	15.85	2.33	32.33	10.23	0.5	0.5	0.5
	nom									13.72										
	min	4.18	0.91	11.58	0.1	31.04	31.14	9.20	9.30		36.22	1.63	16.51	15.65	2.13	32.13	10.03			

sot1251-3_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1251-3						~~14-10-14~~ 14-12-01

Fig 21. Package outline SOT1251-3

9. Handling information

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
IS-95	Interim Standard 95
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC8G27LS-210PV v.1	20150209	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term ‘short data sheet’ is explained in section “Definitions”.

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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13. Contact information

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Date of release: 9 February 2015

Document identifier: BLC8G27LS-210PV